



Product Overview

2N5883: 25 A, 60 V PNP Bipolar Power Transistor

For complete documentation, see the data sheet

Product Description

The Power 25A 80 V Bipolar NPN Transistor is designed for general-purpose power amplifier and switching applications.

Features

- Low Collector-Emitter Saturation Voltage
 $V_{CE(sat)} = 1.0\text{ Vdc}$, (max) at $I_C = 15\text{ Adc}$
- Low Leakage Current
 $I_{CEX} = 1.0\text{ mAdc}$ (max) at Rated Voltage
- Excellent DC Current Gain
 $h_{FE} = 20$ (min) at $I_C = 10\text{ Adc}$
- High Current Gain Bandwidth Product
 $f_t = 4.0\text{ MHz}$ (min) at $I_C = 1.0\text{ Adc}$
- Pb-Free Packages are Available

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{(BR)CEO}$ Min (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
2N5883G	Pb-free	Active	PNP	25	60	20	100	4	200	TO-204-2

For more information please contact your local sales support at www.onsemi.com

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